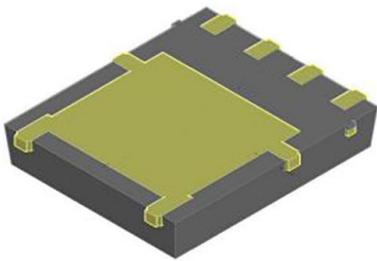


NVMFS6H864NLWFT1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NVMFS6H864NLWFT1G-DG
Manufacturer	onsemi
Manufacturer Product Number	NVMFS6H864NLWFT1G
Description	MOSFET N-CH 80V 7A/22A 5DFN
Detailed Description	N-Channel 80 V 7A (Ta), 22A (Tc) 3.5W (Ta), 33W (Tc) Surface Mount, Wettable Flank 5-DFNW (4.9x5.9) (8-SOFL-WF)

This model NVMFS6H864NLWFT1G is available at DiGi Electronics.

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Purchase and inquiry

Manufacturer Product Number:

NVMFS6H864NLWFT1G

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

80 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2V @ 20 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Qualification:

AEC-Q101

Supplier Device Package:

5-DFNW (4.9x5.9) (8-SOFL-WF)

Base Product Number:

NVMFS6

Manufacturer:

onsemi

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

7A (Ta), 22A (Tc)

Rds On (Max) @ Id, Vgs:

29mOhm @ 5A, 10V

Gate Charge (Qg) (Max) @ Vgs:

9 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

431 pF @ 40 V

Power Dissipation (Max):

3.5W (Ta), 33W (Tc)

Grade:

Automotive

Mounting Type:

Surface Mount, Wettable Flank

Package / Case:

8-PowerTDFN, 5 Leads

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET – Power, Single N-Channel

80 V, 29 mΩ, 22 A

NVMFS6H864NL

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS6H864NLWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	80	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D	22	A
		$T_C = 100^\circ\text{C}$		15	
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^\circ\text{C}$	P_D	33	W
		$T_C = 100^\circ\text{C}$		17	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	7.0	A
		$T_A = 100^\circ\text{C}$		5	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		$T_A = 25^\circ\text{C}$	P_D	3.5	W
		$T_A = 100^\circ\text{C}$		1.7	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	97	A	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	28	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 1.0 \text{ A}$)		E_{AS}	68	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

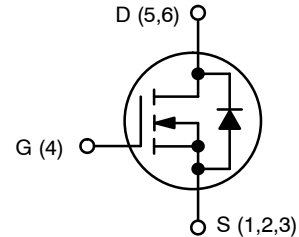
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

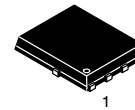
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	4.6	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	43	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

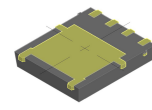
$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
80 V	29 mΩ @ 10 V	22 A
	38 mΩ @ 4.5 V	



N-CHANNEL MOSFET

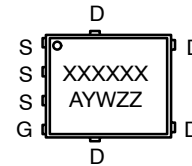


DFN5
(SO-8FL)
CASE 488AA
STYLE 1



DFNW5
(FULL-CUT SO8FL WF)
CASE 507BA

MARKING DIAGRAM



XXXXXX = 6H864L
(NVMFS6H864NL) or
864LWF
(NVMFS6H864NLWF)
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFS6H864NL**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			47.8		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 20\ \mu\text{A}$	1.2		2.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-5.2		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		24	29	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		30	38	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 8\text{ V}, I_D = 5\text{ A}$		24		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$		431		pF	
Output Capacitance	C_{OSS}			55			
Reverse Transfer Capacitance	C_{RSS}			4			
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}; I_D = 10\text{ A}$		9		nC	
Threshold Gate Charge	$Q_{G(TH)}$			1			
Gate-to-Source Charge	Q_{GS}			1.7			
Gate-to-Drain Charge	Q_{GD}			1.4			
Plateau Voltage	V_{GP}			3.2			V
Total Gate Charge	$Q_{G(TOT)}$			4			nC

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 64\text{ V}, I_D = 10\text{ A}, R_G = 2.5\ \Omega$		8		ns
Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(OFF)}$			12		
Fall Time	t_f			4		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 5\text{ A}$	$T_J = 25^\circ\text{C}$		0.82	1.2	V
			$T_J = 125^\circ\text{C}$		0.69		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 10\text{ A}$		25		ns	
Charge Time	t_a			17			
Discharge Time	t_b			8			
Reverse Recovery Charge	Q_{RR}			16			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

NVMFS6H864NL

TYPICAL CHARACTERISTICS

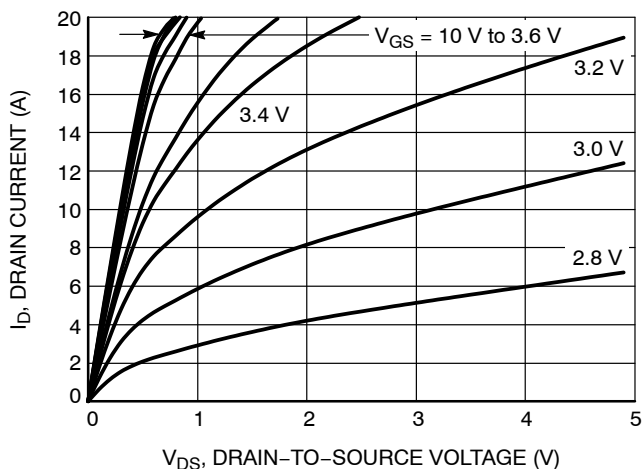


Figure 1. On-Region Characteristics

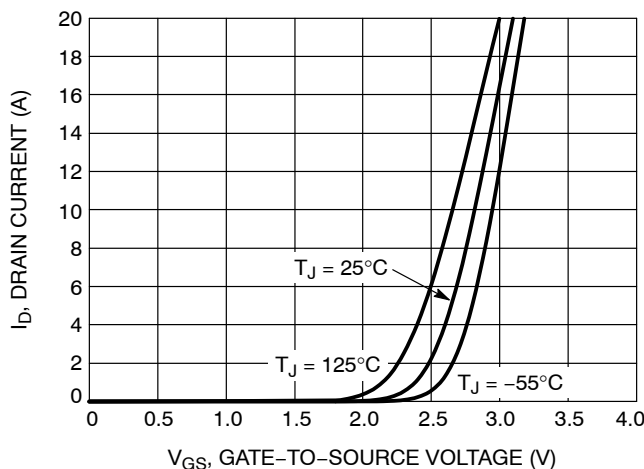


Figure 2. Transfer Characteristics

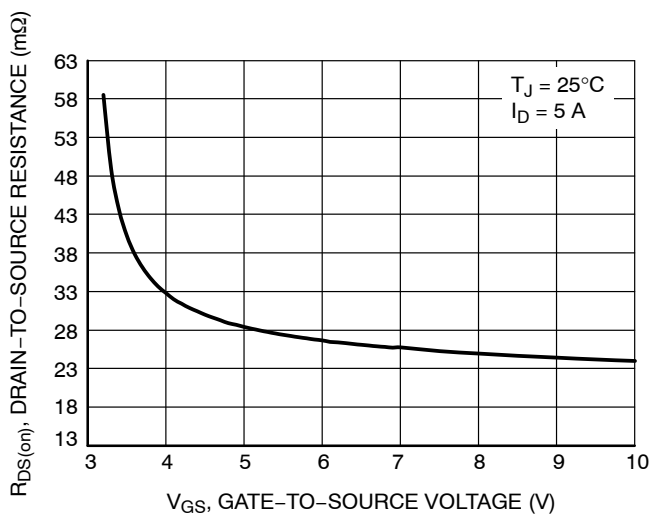


Figure 3. On-Resistance vs. Gate-to-Source Voltage

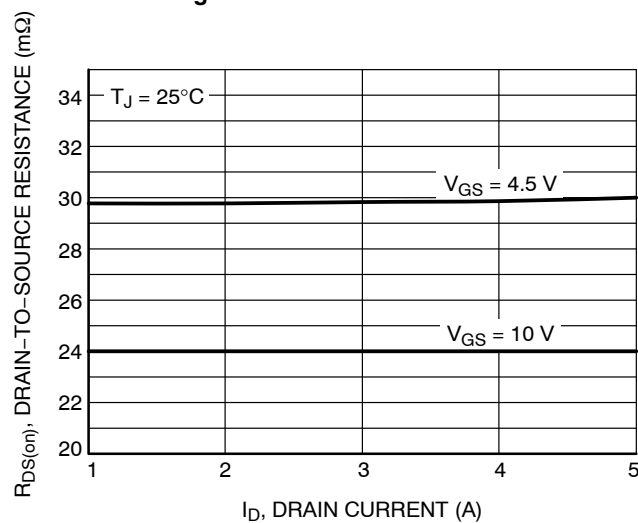


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

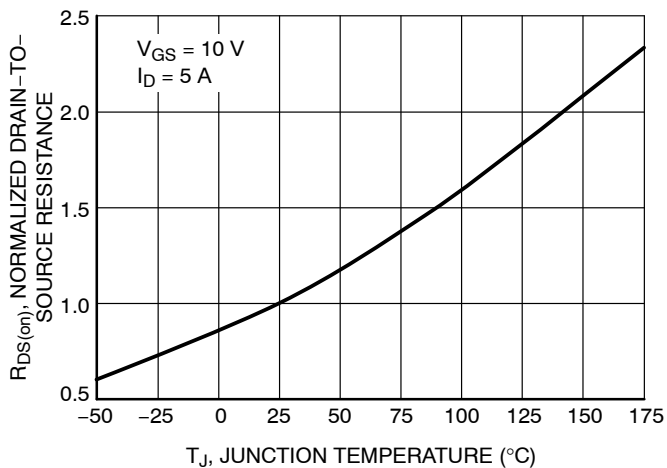


Figure 5. On-Resistance Variation with Temperature

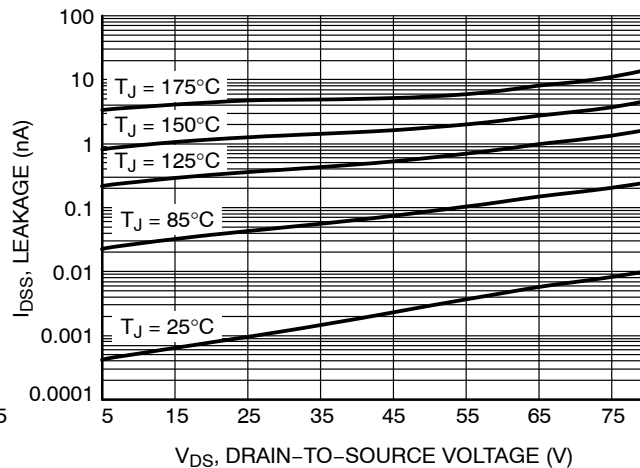


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NVMFS6H864NL

TYPICAL CHARACTERISTICS (Continued)

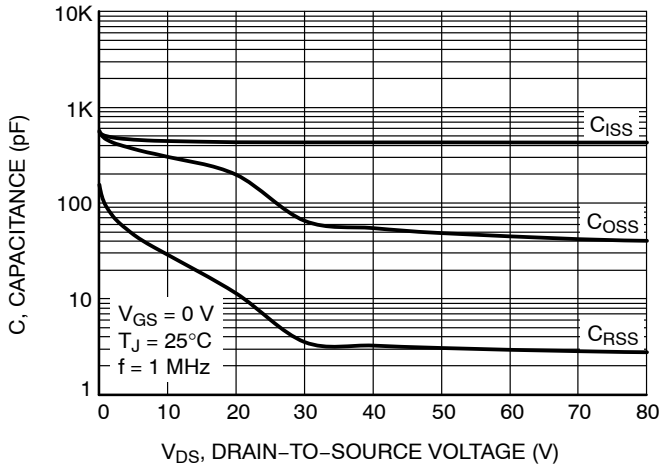


Figure 7. Capacitance Variation

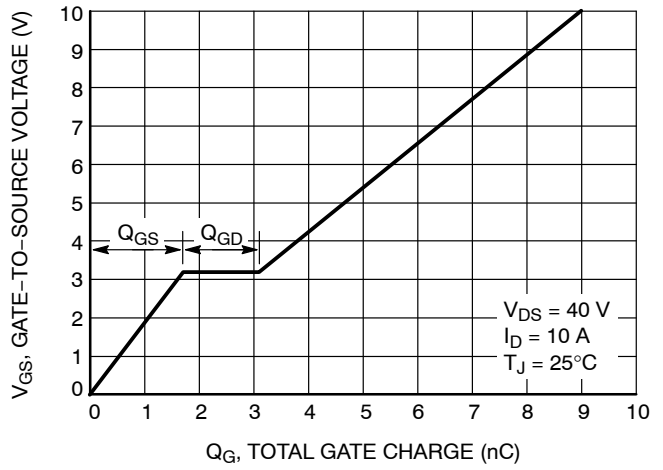


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

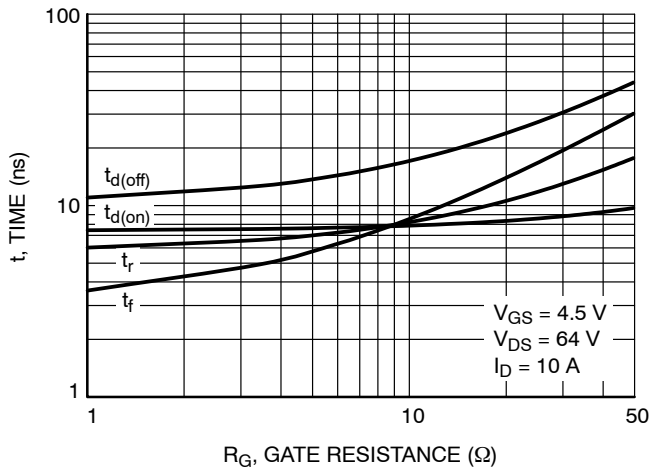


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

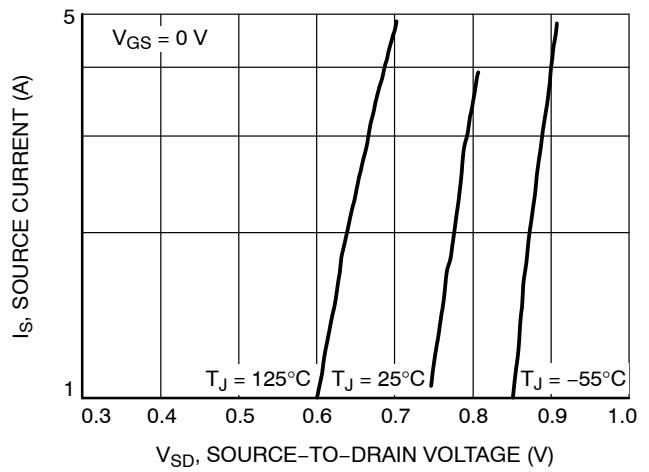


Figure 10. Diode Forward Voltage vs. Current

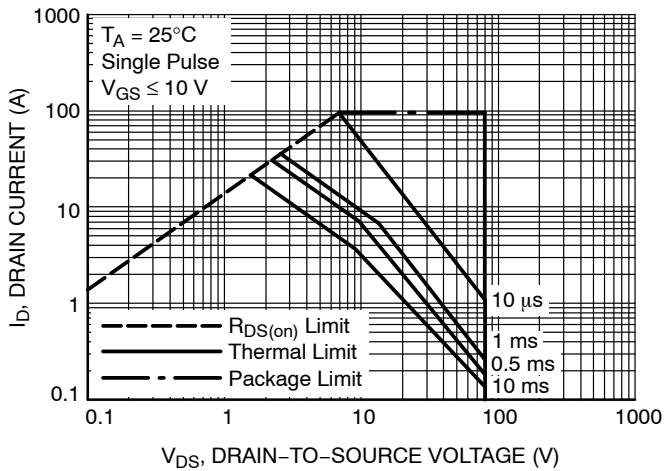


Figure 11. Safe Operating Area

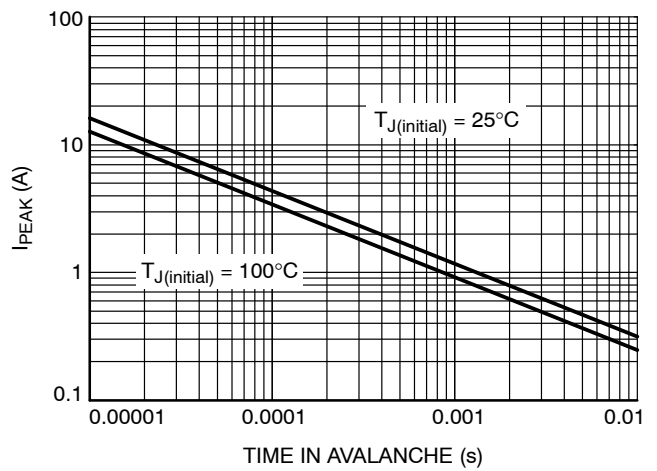


Figure 12. Maximum Drain Current vs. Time in Avalanche

NVMFS6H864NL

TYPICAL CHARACTERISTICS (Continued)

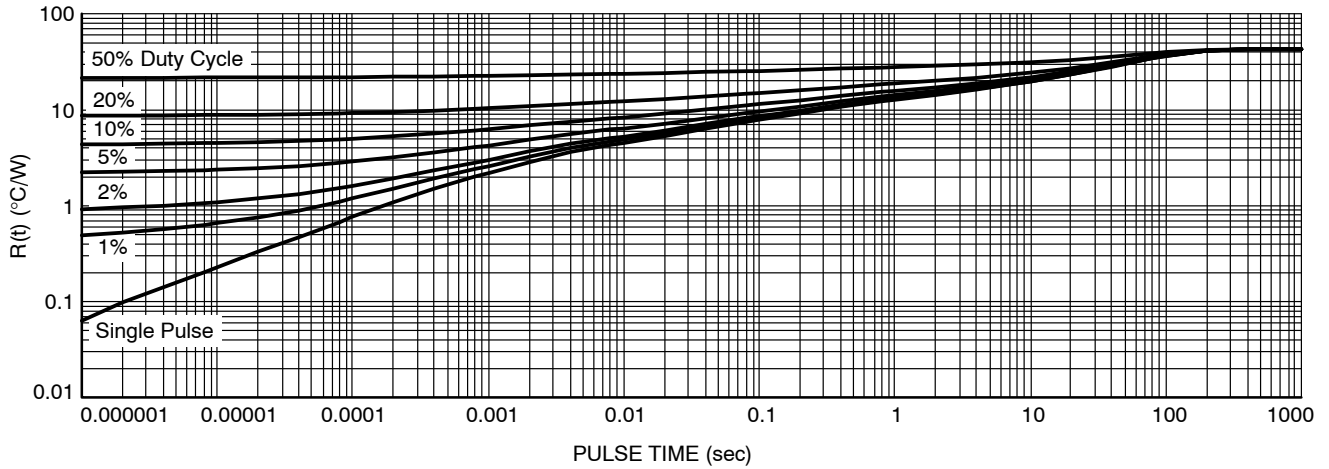


Figure 13. Thermal Response

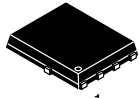
DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFS6H864NLT1G	6H864L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS6H864NLWFT1G	864LWF	DFNW5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).



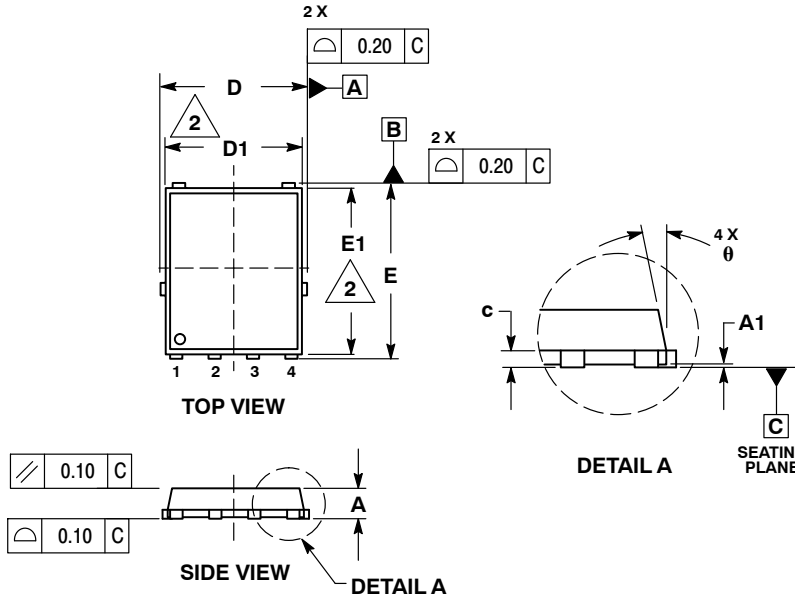
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



1
SCALE 2:1

**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N**

DATE 25 JUN 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

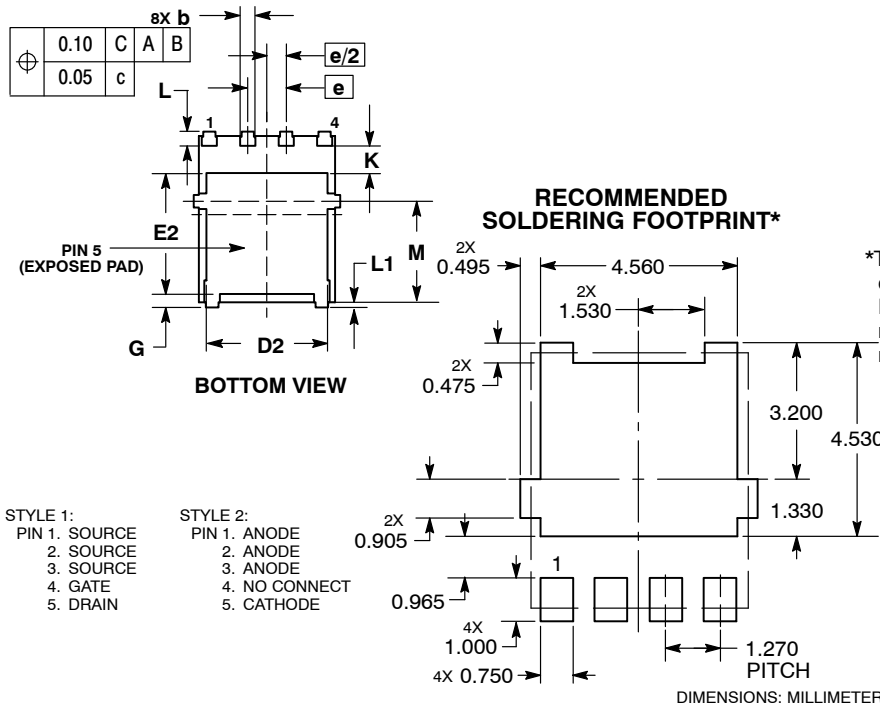
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
theta	0 °	---	12 °

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

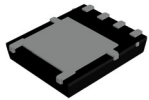
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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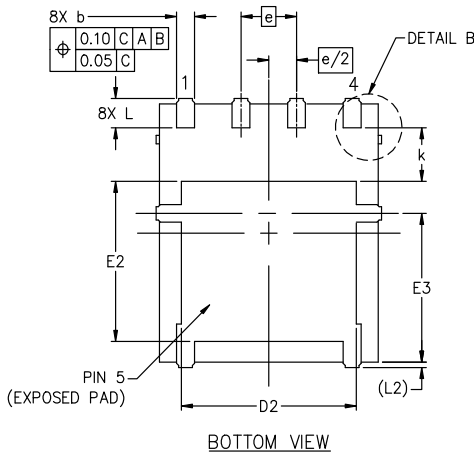
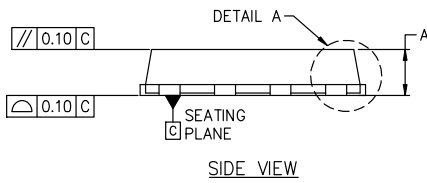
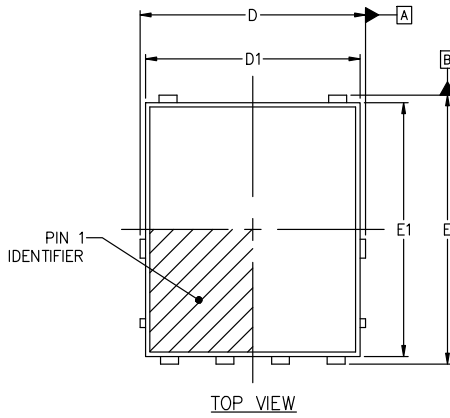


**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



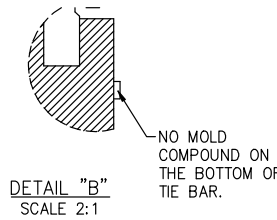
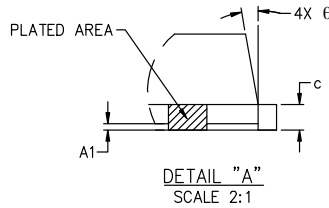
**DFNW5 4.90x5.90x1.00, 1.27P
CASE 507BA
ISSUE C**

DATE 19 SEP 2024

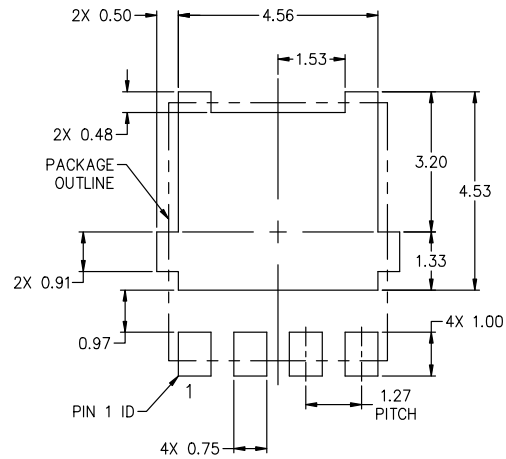


NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
E3	3.00	3.40	3.80
e	1.27 BSC		
k	1.20	1.35	1.50
L	0.51	0.57	0.71
L2	0.15 REF.		
theta	0°	6°	12°



RECOMMENDED MOUNTING FOOTPRINT*
*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DFNW5 4.90x5.90x1.00, 1.27P	PAGE 1 OF 1

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